

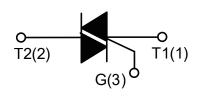
DESCRIPTION:

The BT137S-600F SCR series with the parallel resistor between Gate and Cathode are especially recommended for use on straight hair, igniter, anion generator, etc.



MAIN FEATURES

Symbol	Value	Unit
I _{T(RMS)}	8	А
V _{DRM} /V _{RRM}	600/800	V



ABSOLUTE MAXIMUM RATINGS

Parameter			Symbol	Value	Unit	
Storage junction temperature range			T _{stg}	-40-150	$^{\circ}\mathbb{C}$	
Operating junction tem	perature r	perature range		-40-125	$^{\circ}\mathbb{C}$	
Repetitive peak off-stat	te voltage	(T _j =25℃)	V _{DRM}	600/800	V	
Repetitive peak reverse voltage(T _j =25℃)			V _{RRM}	600/800	V	
RMS on-state current	TO-252 (T _C =103°C) TO-263 (T _C =85°C)		I _{T(RMS)}	8	А	
Non repetitive surge peak on-state current (full cycle, F=50Hz)			Ітѕм	65	Α	
I ² t value for fusing (tp=10ms)			l ² t	21	A ² s	
Peak gate current			l _{GM}	2	А	
Critical rate of rise of on-state current(I _G =2×I _{GT})		I - II -III	d1/d+	50	A/µs	
		IV	- dl/dt	10		
Average gate power dissipation			P _{G(AV)}	0.5	W	
Peak gate power			P _{GM}	5	W	



ELECTRICAL CHARACTERISTICS (T_j=25 °C unless otherwise specified)

Symbol	Test Condition	Quadrant		Value			I Incit	
Symbol				D	Е	F	G	Unit
I _{GT}	V _D =12V R _L =30Ω	I - II -III	MAX	5	10	25	50	mA
IGI		IV		10	25	70	100	
V _G T		ALL	MAX	1.3				V
V _{GD}	$V_D=V_{DRM}$ $T_j=125$ $^{\circ}$ C ALL RL=3.3KΩ		MIN	0.2			V	
IL	I _G =1.2I _{GT}	I -III	MAX	10	20	50	70	mA
		II -IV	IVIAA	20	30	70	100	IIIA
Ін	I _T =100mA		MAX	10	15	40	60	mA
dV/dt	V _D =2/3V _{DRM} Gate Open T _j =125℃		MIN	20	50	50	200	V/µs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V _{TM}	I _{тм} =10A tp=380µs	T _j =25℃	1.6	V
IDRM	V _D =V _{DRM} V _R =V _{RRM}	T _j =25℃	5	μA
I _{RRM}		T _j =125℃	1	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth(j-c)	junction to case(AC)	TO-252 2.1		°C/W
		TO-263	3.1	
R _{th(j-a)}	junction to ambient	TO-252 70		~ °C/W
		TO-263	45	



FIG.1: Maximum power dissipation versus RMS on-state current

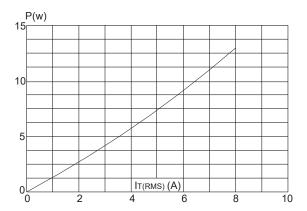


FIG.3: Surge peak on-state current versus number of cycles

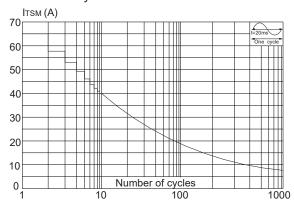


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35µm)(full cycle)

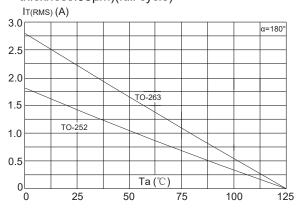


FIG.4: On-state characteristics (maximum values)

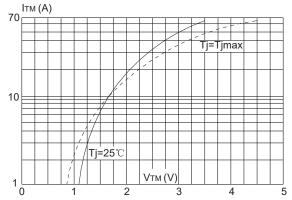




FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t ($I - II - III : dI/dt < 50A/\mu s$; $IV : dI/dt < 10A/\mu s$)

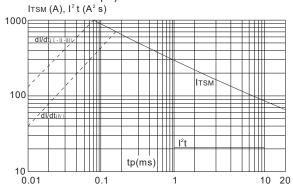


FIG.7: Relative variations of holding current versus junction temperature

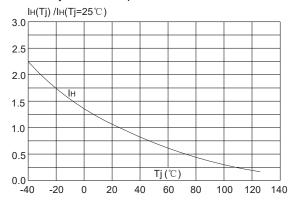


FIG.6: Relative variations of gate trigger current versus junction temperature

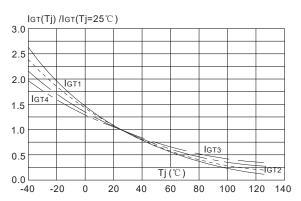
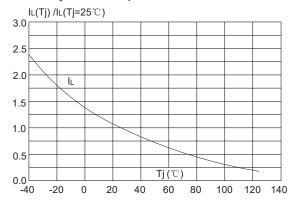


FIG.8: Relative variations of latching current versus junction temperature





SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly		
		(see figure at right)		
	-Temperature Min	+150℃		
	(T _{s(min)})	1130 C		
Pre	-Temperature Max	+200℃		
Heat	(T _{s(max)})	1200 €		
	-Time (Min to Max)	60-180 secs.		
	(ts)	00-100 Secs.		
Average i	ramp up rate	3°C/sec. Max		
(Liquidus	Temp (T∟)to peak)	3 C/Sec. Max		
T _{s(max)} to T _L - Ramp-up Rate		3℃/sec. Max		
	-Temperature(T∟)	+217 ℃		
Reflow	(Liquidus)	2		
	-Temperature(t _L)	60-150 secs.		
Peak Ten	1p (T _p)	+260(+0/-5)°C		
Time with	in 5°Cof actual	20-40secs.		
Peak Ten	np (t _p)	20-403663.		
Ramp-do	wn Rate	6°C/sec. Max		
Time 25°	to Peak Temp (T _P)	8 min. Max		
Do not ex	cceed	+260℃		

